



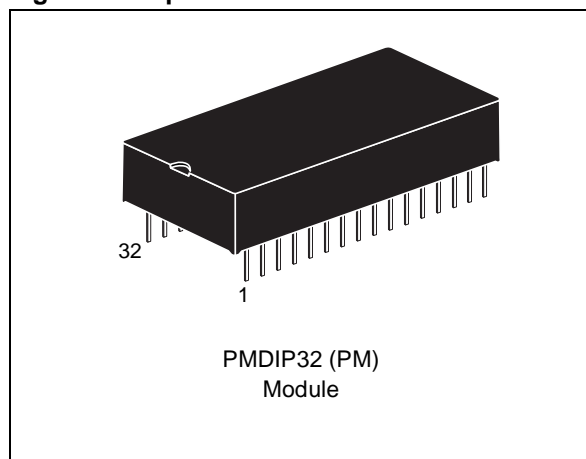
M48Z128 M48Z128Y, M48Z128V*

5.0V OR 3.3V, 1 Mbit (128 Kbit x 8) ZEROPOWER[®] SRAM

FEATURES SUMMARY

- INTEGRATED, ULTRA LOW POWER SRAM, POWER-FAIL CONTROL CIRCUIT, and BATTERY
- CONVENTIONAL SRAM OPERATION; UNLIMITED WRITE CYCLES
- 10 YEARS OF DATA RETENTION IN THE ABSENCE OF POWER
- BATTERY INTERNALLY ISOLATED UNTIL POWER IS FIRST APPLIED
- AUTOMATIC POWER-FAIL CHIP DESELECT and WRITE PROTECTION
- WRITE PROTECT VOLTAGES:
(V_{PFD} = Power-fail Deselect Voltage)
 - M48Z128: $V_{CC} = 4.75$ to $5.5V$
 $4.5V \leq V_{PFD} \leq 4.75V$
 - M48Z128Y: $V_{CC} = 4.5$ to $5.5V$
 $4.2V \leq V_{PFD} \leq 4.5V$
 - M48Z128V: $V_{CC} = 3.0$ to $3.6V$
 $2.8V \leq V_{PFD} \leq 3.0V$
- SOIC PACKAGE PROVIDES DIRECT CONNECTION FOR A SNAPHAT TOP WHICH CONTAINS THE BATTERY
- SNAPHAT HOUSING (BATTERY) IS REPLACEABLE
- PIN and FUNCTION COMPATIBLE WITH JEDEC STANDARD 128K x 8 SRAMs
- EQUIVALENT SURFACE-MOUNT (SMT) SOLUTION REQUIRES A 28-PIN M40Z300/W and A STAND-ALONE 128K x8 LPSRAM (SNAPHAT[®] Top to be ordered separately)

Figure 1. 32-pin PMDIP Module



* Contact Local Sales Office

TABLE OF CONTENTS

| | |
|---|-----------|
| DESCRIPTION | 3 |
| Logic Diagram (Figure 2.) | 3 |
| Signal Names (Table 1.) | 3 |
| DIP Connections (Figure 3.) | 4 |
| Block Diagram (Figure 4.) | 4 |
| Hardware Hookup for Equivalent Surface-Mount (SMT) Solution (Figure 5.) | 5 |
| Equivalent Surface-Mount (SMT) Solution (Table 2.) | 5 |
| MAXIMUM RATING | 6 |
| Absolute Maximum Ratings (Table 3.) | 6 |
| DC AND AC PARAMETERS | 7 |
| Operating and AC Measurement Conditions (Table 4.) | 7 |
| AC Measurement Load Circuit (Figure 6.) | 7 |
| Capacitance (Table 5.) | 7 |
| DC Characteristics (Table 6.) | 8 |
| OPERATING MODES | 8 |
| Operating Modes (Table 7.) | 8 |
| READ Mode | 9 |
| Chip Enable or Output Enable Controlled, READ Mode AC Waveforms (Figure 7.) | 9 |
| Address Controlled, READ Mode AC Waveforms (Figure 8.) | 9 |
| READ Mode AC Characteristics (Table 8.) | 10 |
| WRITE Mode | 11 |
| WRITE Enable Controlled, WRITE AC Waveforms (Figure 9.) | 11 |
| Chip Enable Controlled, WRITE AC Waveforms (Figure 10.) | 11 |
| WRITE Mode AC Characteristics (Table 9.) | 12 |
| Data Retention Mode | 13 |
| Power Down/Up Mode AC Waveforms (Figure 11.) | 13 |
| Power Down/Up AC Characteristics (Table 10.) | 13 |
| Power Down/Up Trip Points DC Characteristics (Table 11.) | 14 |
| V_{CC} Noise And Negative Going Transients | 14 |
| Supply Voltage Protection (Figure 12.) | 14 |
| PART NUMBERING | 15 |
| SNAPHAT Battery Table (Table 13.) | 15 |
| PACKAGE MECHANICAL INFORMATION | 16 |
| REVISION HISTORY | 20 |

DESCRIPTION

The M48Z128/Y/V ZEROPOWER® RAM is a 128 Kbit x 8 non-volatile static RAM organized as 131,072 words by 8 bits. The device combines an internal lithium battery, a CMOS SRAM and a control circuit in a plastic, 32-pin DIP module. This solution is available in two special packages to provide a highly integrated battery backed-up memory solution.

The M48Z128/Y/V is a non-volatile pin and function equivalent to any JEDEC standard 128K x 8 SRAM. It also easily fits into many ROM, EPROM, and EEPROM sockets, providing the non-volatility of PROMs without any requirement for special WRITE timing or limitations on the number of WRITES that can be performed. The 32-pin, 600mil DIP Module houses the M48Z128/Y/V silicon with a long life lithium button cell in a single package.

For surface-mount environments ST provides an equivalent SMT solution consisting of a 28-pin, 330mil SOIC NVRAM SUPERVISOR (M40Z300/

W) and a 32-pin, (TSOP, 8 x 20mm) 1Mb LPSRAM. Both 5V and 3V versions are available (see Table 2, page 5).

The 28-pin, 330mil SOIC provides sockets with gold plated contacts at both ends for direct connection to a separate SNAPHAT® housing containing the battery.

The unique design allows the SNAPHAT battery package to be mounted on top of the SOIC package after the completion of the surface-mount process. Insertion of the SNAPHAT housing after reflow prevents potential battery damage due to the high temperatures required for device surface-mounting. The SNAPHAT housing is keyed to prevent reverse insertion.

The SNAPHAT battery package is shipped separately in plastic anti-static tubes or in Tape & Reel form. The part number is "M4Zxx-BR00SH" (see Table 13, page 15).

Figure 2. Logic Diagram

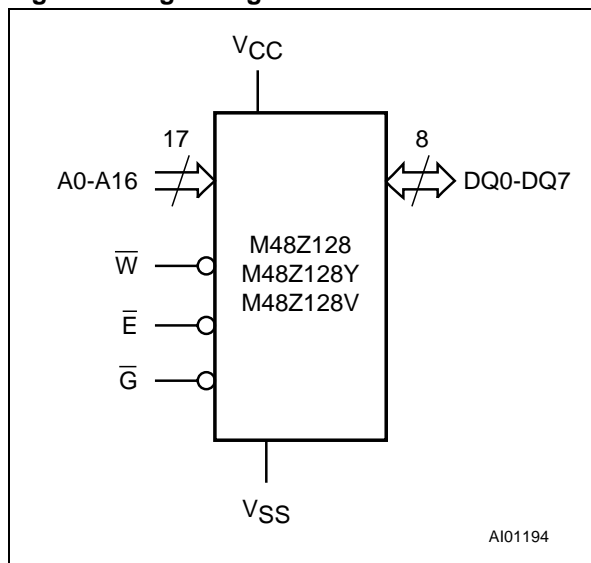


Table 1. Signal Names

| | |
|-----------------|--------------------------|
| A0-A16 | Address Inputs |
| DQ0-DQ7 | Data Inputs / Outputs |
| \bar{E} | Chip Enable Input |
| \bar{G} | Output Enable Input |
| \bar{W} | WRITE Enable Input |
| V _{CC} | Supply Voltage |
| V _{SS} | Ground |
| NC | Not Connected Internally |

Figure 3. DIP Connections

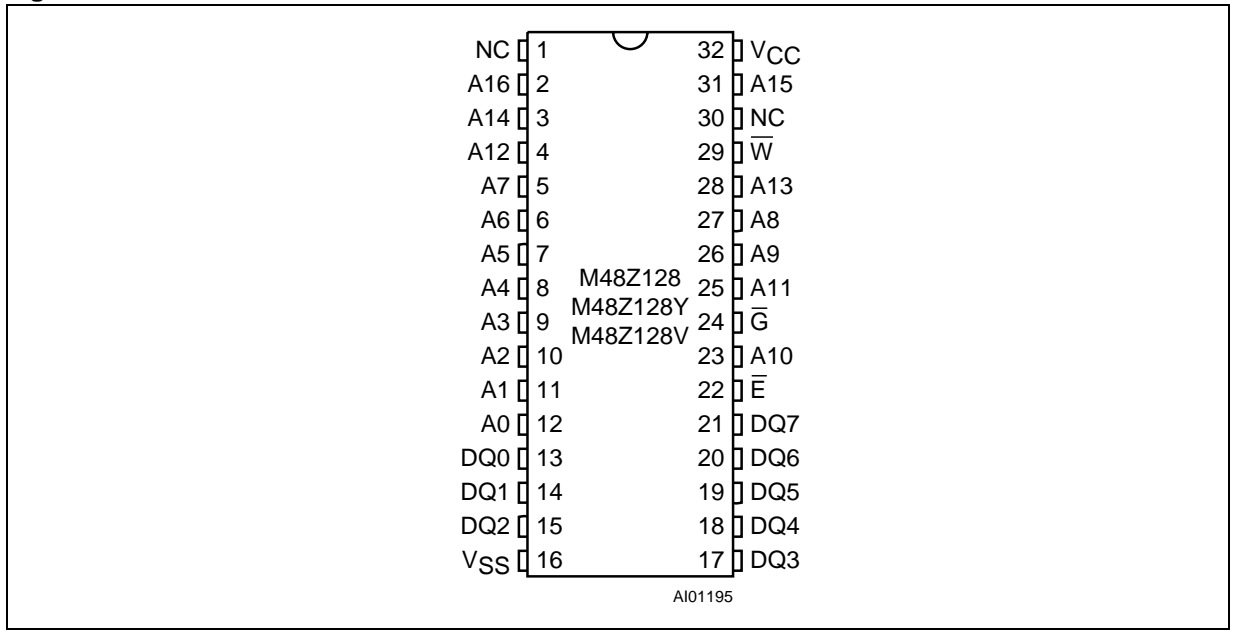


Figure 4. Block Diagram

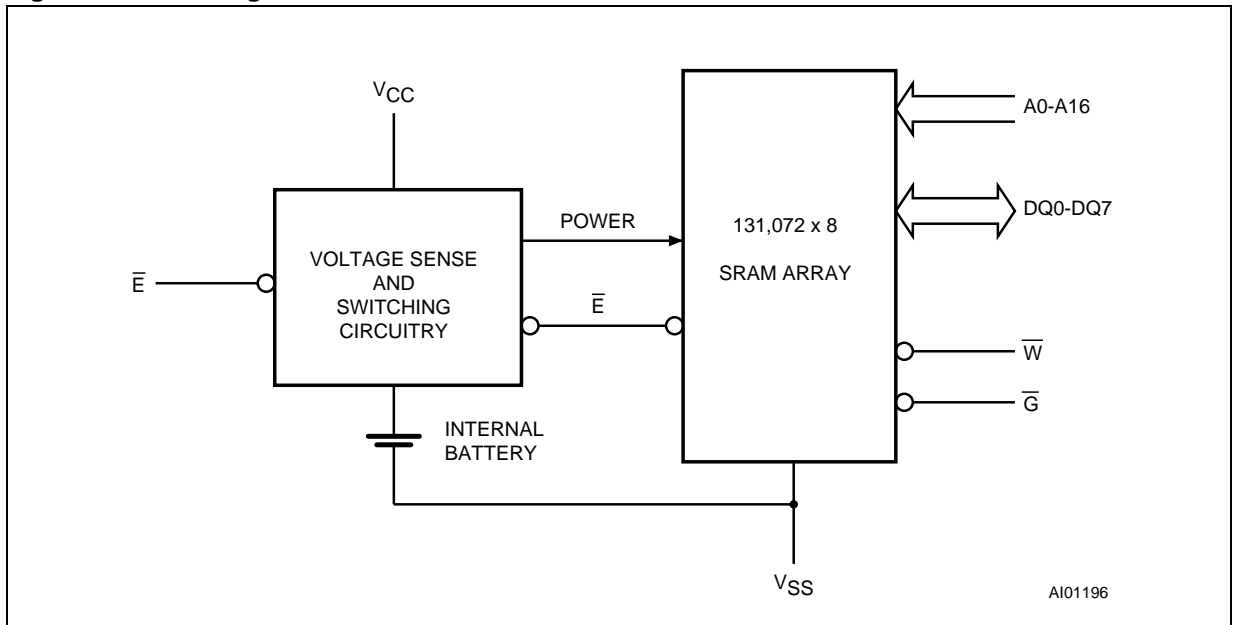
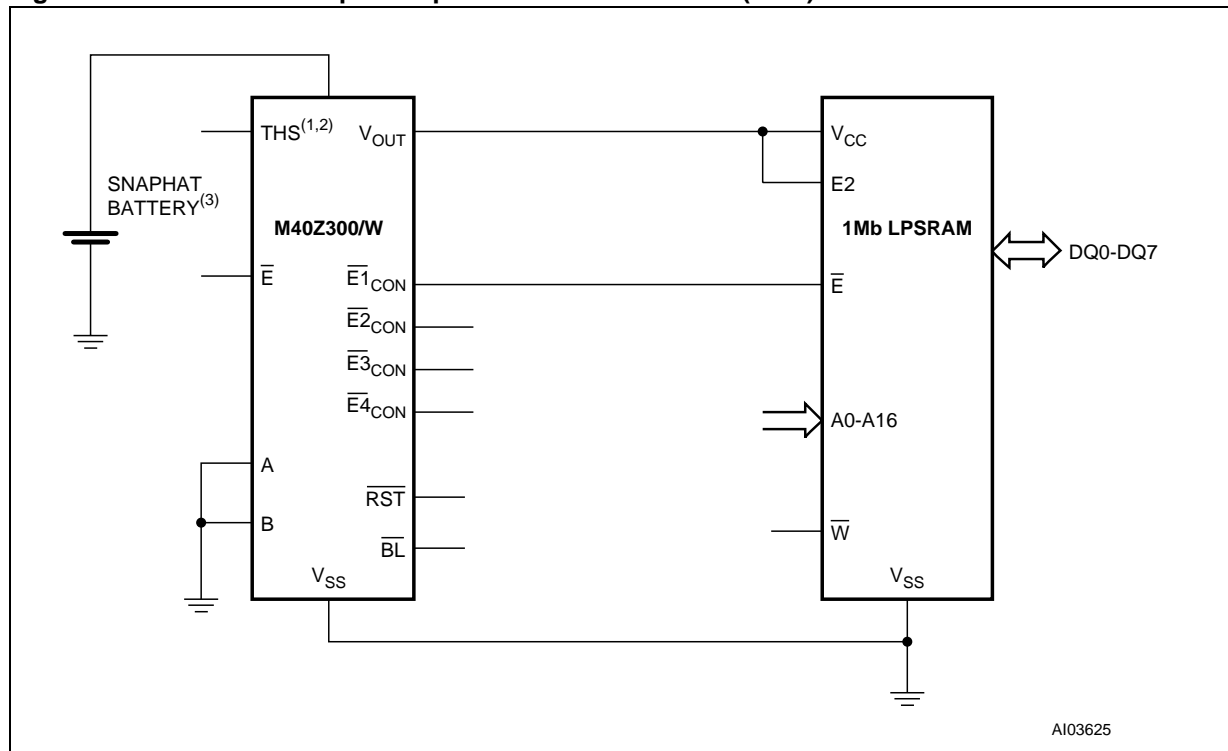


Figure 5. Hardware Hookup for Equivalent Surface-Mount (SMT) Solution



Note: For pin connections, see individual data sheet for M48Z300/300W at www.st.com.

1. Connect THS pin to V_{OUT} if $4.2V \leq V_{PFD} \leq 4.5V$ (M48Z128Y) or connect THS pin to V_{SS} if $4.5V \leq V_{PFD} \leq 4.75V$ (M48Z128).
2. Connect THS pin to V_{SS} if $2.8V \leq V_{PFD} \leq 3.0V$ (M48Z128V).
3. SNAPHAT® Top ordered separately.

Table 2. Equivalent Surface-Mount (SMT) Solution

| NVRAM | LPSRAM | SUPERVISOR | THS Pin ⁽¹⁾ |
|----------|---------------|------------|------------------------|
| M48Z128 | 5V 1Mb LPSRAM | M40Z300 | V _{SS} |
| M48Z128Y | 5V 1Mb LPSRAM | M40Z300 | V _{OUT} |
| M48Z128V | 3V 1Mb LPSRAM | M40Z300W | V _{SS} |

Note: 1. Connection of Threshold Select Pin (Pin 13) of SUPERVISOR (M40Z300/300W).

MAXIMUM RATING

Stressing the device above the rating listed in the “Absolute Maximum Ratings” table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is

not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Table 3. Absolute Maximum Ratings

| Symbol | Parameter | Value | Unit |
|-----------------------------------|---|-----------|-------------|
| T _A | Ambient Operating Temperature | 0 to 70 | °C |
| T _{STG} | Storage Temperature (V _{CC} Off, Oscillator Off) | −40 to 85 | °C |
| T _{BIAS} | Temperature Under Bias | −10 to 70 | °C |
| T _{SLD} ^(1,2) | Lead Solder Temperature for 10 seconds | 260 | °C |
| V _{IO} | Input or Output Voltages | −0.3 to 7 | V |
| V _{CC} | Supply Voltage | M48Z128/Y | −0.3 to 7.0 |
| | | M48Z128V | −0.3 to 4.6 |
| I _O | Output Current | 20 | mA |
| P _D | Power Dissipation | 1 | W |

Note: 1. For DIP package: Soldering temperature not to exceed 260°C for 10 seconds (total thermal budget not to exceed 150°C for longer than 30 seconds).

2. For SO package: Reflow at peak temperature of 215°C to 225°C for < 60 seconds (total thermal budget not to exceed 180°C for between 90 to 120 seconds).

CAUTION: Negative undershoots below −0.3V are not allowed on any pin while in the Battery Back-up mode.

CAUTION: Do NOT wave solder SOIC to avoid damaging SNAPHAT sockets.

DC AND AC PARAMETERS

This section summarizes the operating and measurement conditions, as well as the DC and AC characteristics of the device. The parameters in the following DC and AC Characteristic tables are derived from tests performed under the Measure-

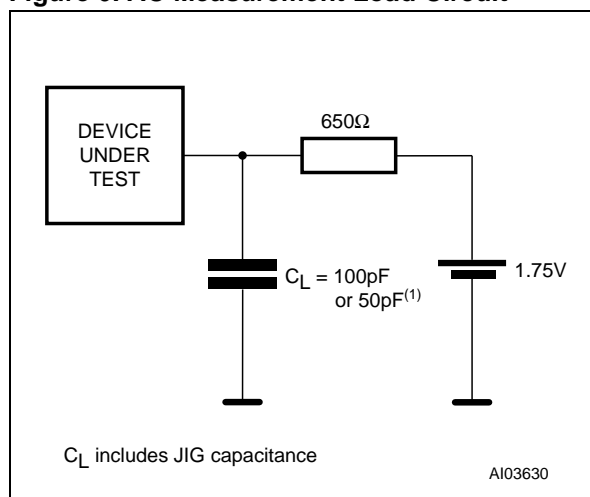
ment Conditions listed in the relevant tables. Designers should check that the operating conditions in their projects match the measurement conditions when using the quoted parameters.

Table 4. Operating and AC Measurement Conditions

| Parameter | M48Z128/Y | M48Z128V | Unit |
|---|----------------------------|------------|------|
| Supply Voltage (V_{CC}) | 4.75 to 5.5V or 4.5 to 5.5 | 3.0 to 3.6 | V |
| Ambient Operating Temperature (T_A) | 0 to 70 | 0 to 70 | °C |
| Load Capacitance (C_L) | 100 | 50 | pF |
| Input Rise and Fall Times | ≤ 5 | ≤ 5 | ns |
| Input Pulse Voltages | 0 to 3 | 0 to 3 | V |
| Input and Output Timing Ref. Voltages | 1.5 | 1.5 | V |

Note: Output Hi-Z is defined as the point where data is no longer driven.

Figure 6. AC Measurement Load Circuit



Note: 1. 50pF for M48Z128V (3.3V).

Table 5. Capacitance

| Symbol | Parameter ^(1,2) | Min | Max | Unit |
|----------------|----------------------------|-----|-----|------|
| C_{IN} | Input Capacitance | | 10 | pF |
| $C_{IO}^{(3)}$ | Input / Output Capacitance | | 10 | pF |

Note: 1. Effective capacitance measured with power supply at 5V (M48Z128/Y) or 3.3V (M48Z128V); sampled only, not 100% tested.
 2. At 25°C, $f = 1\text{MHz}$.
 3. Outputs deselected.

Table 6. DC Characteristics

| Sym | Parameter | Test Condition ⁽¹⁾ | M48Z128/Y | | M48Z128V | | Unit |
|--------------------------------|-------------------------------|---|------------------|-----------------------|------------|-----------------------|------|
| | | | -70 / -85 / -120 | | -85 / -120 | | |
| | | | Min | Max | Min | Max | |
| I _{LI} | Input Leakage Current | 0V ≤ V _{IN} ≤ V _{CC} | | ±1 | | ±1 | μA |
| I _{LO} ⁽²⁾ | Output Leakage Current | 0V ≤ V _{OUT} ≤ V _{CC} | | ±1 | | ±1 | μA |
| I _{CC} | Supply Current | $\bar{E} = V_{IL}$ Outputs open | | 105 | | 50 | mA |
| I _{CC1} | Supply Current (Standby) TTL | $\bar{E} = V_{IH}$ | | 7 | | 4 | mA |
| I _{CC2} | Supply Current (Standby) CMOS | $\bar{E} = V_{CC} - 0.2V$ | | 4 | | 3 | mA |
| V _{IL} | Input Low Voltage | | -0.3 | 0.8 | -0.3 | 0.6 | V |
| V _{IH} | Input High Voltage | | 2.2 | V _{CC} + 0.3 | 2.2 | V _{CC} + 0.3 | V |
| V _{OL} | Output Low Voltage | I _{OL} = 2.1mA | | 0.4 | | 0.4 | V |
| V _{OH} | Output High Voltage | I _{OH} = -1mA | 2.4 | | 2.2 | | V |

Note: 1. Valid for Ambient Operating Temperature: T_A = 0 to 70°C; V_{CC} = 4.75 to 5.5V, 4.5 to 5.5V, or 3.0 to 3.6V (except where noted).
2. Outputs deselected.

OPERATING MODES

The M48Z128/Y/V also has its own Power-fail Detect circuit. The control circuitry constantly monitors the single V_{CC} supply for an out of tolerance condition. When V_{CC} is out of tolerance, the circuit write protects the SRAM, providing a high degree

of data security in the midst of unpredictable system operation brought on by low V_{CC}. As V_{CC} falls below the switchover voltage (V_{SO}), the control circuitry connects the battery which maintains data until valid power returns.

Table 7. Operating Modes

| Mode | V _{CC} | \bar{E} | \bar{G} | \bar{W} | DQ0-DQ7 | Power |
|----------|--|-----------------|-----------------|-----------------|------------------|----------------------|
| Deselect | 4.75 to 5.5V or 4.5 to 5.5V or 3.0 to 3.6V | V _{IH} | X | X | High Z | Standby |
| WRITE | | V _{IL} | X | V _{IL} | D _{IN} | Active |
| READ | | V _{IL} | V _{IL} | V _{IH} | D _{OUT} | Active |
| READ | | V _{IL} | V _{IH} | V _{IH} | High Z | Active |
| Deselect | V _{SO} to V _{PFD} (min) ⁽¹⁾ | X | X | X | High Z | CMOS Standby |
| Deselect | ≤ V _{SO} ⁽¹⁾ | X | X | X | High Z | Battery Back-up Mode |

Note: X = V_{IH} or V_{IL}; V_{SO} = Battery Back-up Switchover Voltage.

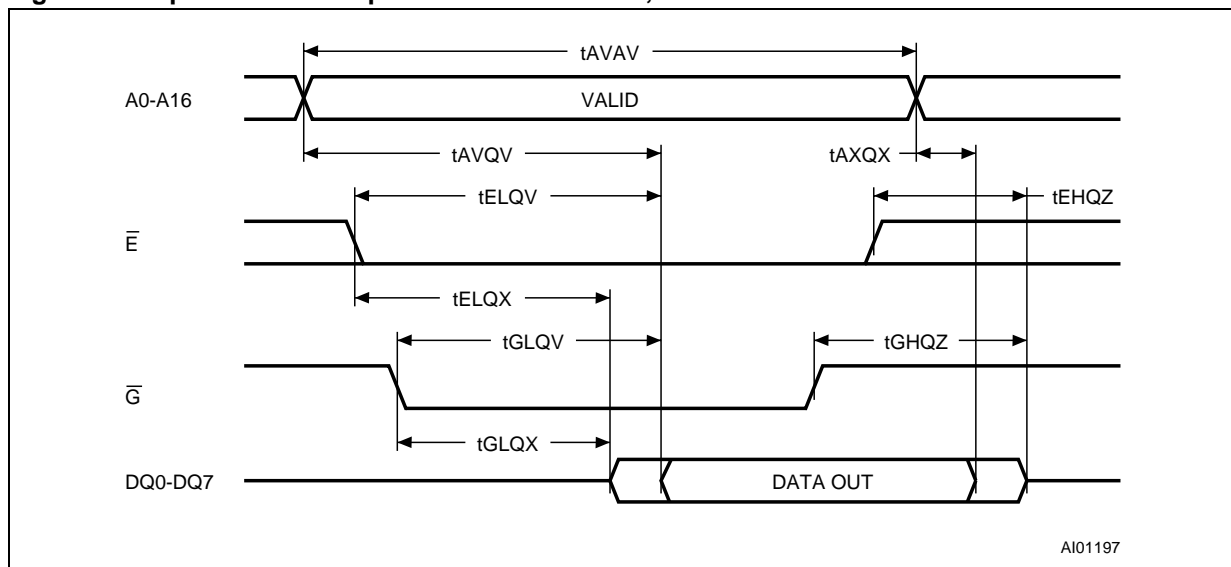
1. See Table 11, page 14 for details.

READ Mode

The M48Z128/Y/V is in the READ Mode whenever \overline{W} (WRITE Enable) is high and \overline{E} (Chip Enable) is low. The device architecture allows ripple-through access of data from eight of 1,048,576 locations in the static storage array. Thus, the unique address specified by the 17 address inputs defines which one of the 131,072 bytes of data is to be accessed. Valid data will be available at the Data I/O pins within Address Access time (t_{AVQV}) after the last address input signal is stable, providing that the \overline{E} and \overline{G} (Output Enable) access times are also sat-

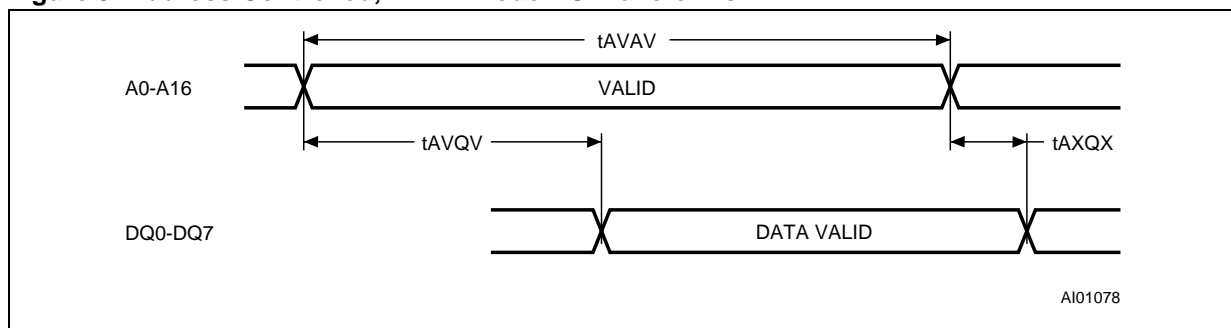
isfied. If the \overline{E} and \overline{G} access times are not met, valid data will be available after the later of Chip Enable Access time (t_{ELQV}) or Output Enable Access Time (t_{GLQV}). The state of the eight three-state Data I/O signals is controlled by \overline{E} and \overline{G} . If the outputs are activated before t_{AVQV} , the data lines will be driven to an indeterminate state until t_{AVQV} . If the address inputs are changed while \overline{E} and \overline{G} remain low, output data will remain valid for Output Data Hold time (t_{AXQX}) but will go indeterminate until the next Address Access.

Figure 7. Chip Enable or Output Enable Controlled, READ Mode AC Waveforms



Note: WRITE Enable (\overline{W}) = High.

Figure 8. Address Controlled, READ Mode AC Waveforms



Note: Chip Enable (\overline{E}) and Output Enable (\overline{G}) = Low, WRITE Enable (\overline{W}) = High.

Table 8. READ Mode AC Characteristics

| Symbol | Parameter ⁽¹⁾ | M48Z128/Y | | M48Z128/Y/V | | M48Z128/Y/V | | Unit |
|----------------------------------|---|-----------|-----|-------------|-----|-------------|-----|------|
| | | -70 | | -85 | | -120 | | |
| | | Min | Max | Min | Max | Min | Max | |
| t _{AVAV} | READ Cycle Time | 70 | | 85 | | 120 | | ns |
| t _{AVQV} | Address Valid to Output Valid | | 70 | | 85 | | 120 | ns |
| t _{ELQV} | Chip Enable Low to Output Valid | | 70 | | 85 | | 120 | ns |
| t _{GLQV} | Output Enable Low to Output Valid | | 35 | | 45 | | 60 | ns |
| t _{ELQX} ⁽²⁾ | Chip Enable Low to Output Transition | 5 | | 5 | | 5 | | ns |
| t _{GLQX} ⁽²⁾ | Output Enable Low to Output Transition | 3 | | 3 | | 3 | | ns |
| t _{EHQZ} ⁽²⁾ | Chip Enable High to Output Hi-Z | | 30 | | 35 | | 45 | ns |
| t _{GHQZ} ⁽²⁾ | Output Enable High to Output Hi-Z | | 20 | | 25 | | 35 | ns |
| t _{AXQX} | Address Transition to Output Transition | 5 | | 5 | | 10 | | ns |

Note: 1. Valid for Ambient Operating Temperature: T_A = 0 to 70°C; V_{CC} = 4.75 to 5.5V, 4.5 to 5.5V, or 3.0 to 3.6V (except where noted).

2. C_L = 5pF.

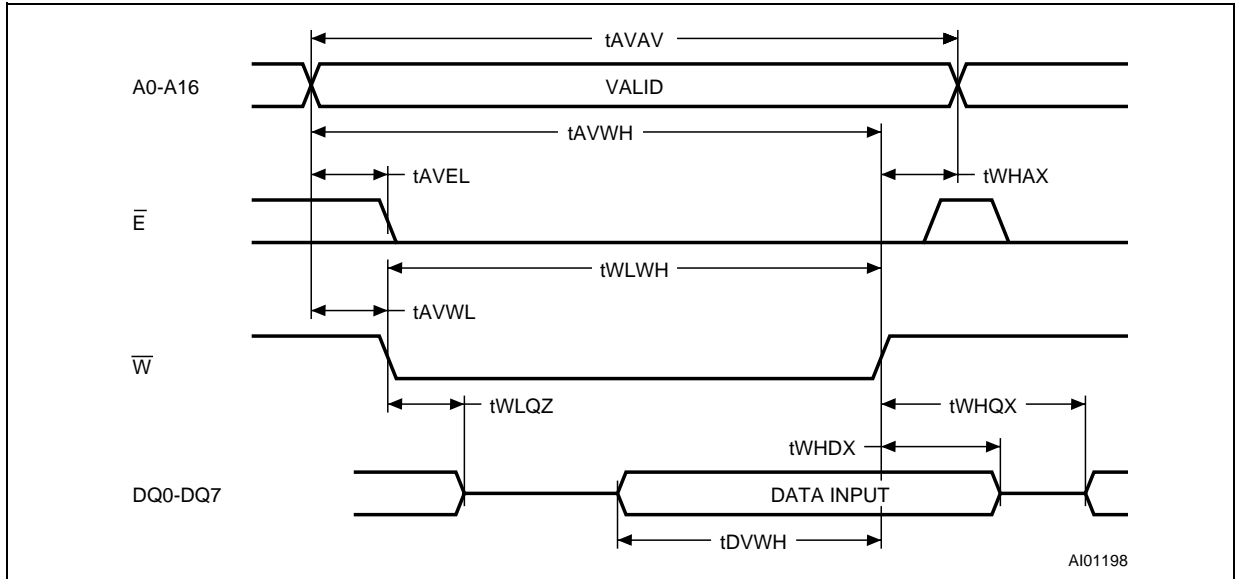
WRITE Mode

The M48Z128/Y/V is in the WRITE Mode whenever \overline{W} and \overline{E} are active. The start of a WRITE is referenced from the latter occurring falling edge of \overline{W} or \overline{E} . A WRITE is terminated by the earlier rising edge of \overline{W} or \overline{E} .

The addresses must be held valid throughout the cycle. \overline{E} or \overline{W} must return high for minimum of t_{EHAX} from \overline{E} or t_{WHAX} from \overline{W} prior to the initiation

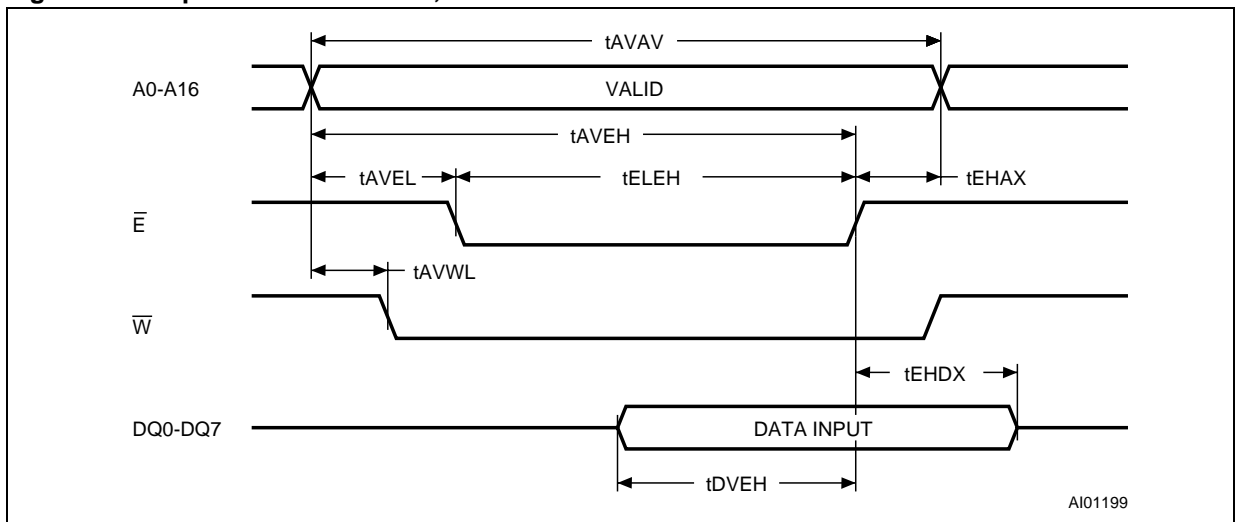
of another READ or WRITE cycle. Data-in must be valid t_{DVWH} prior to the end of WRITE and remain valid for t_{WHDX} or t_{EHDX} afterward. \overline{G} should be kept high during WRITE cycles to avoid bus contention; although, if the output bus has been activated by a low on \overline{E} and \overline{G} , a low on \overline{W} will disable the outputs t_{WLQZ} after \overline{W} falls.

Figure 9. WRITE Enable Controlled, WRITE AC Waveforms



Note: Output Enable (\overline{G}) = High.

Figure 10. Chip Enable Controlled, WRITE AC Waveforms



Note: Output Enable (\overline{G}) = High.

Table 9. WRITE Mode AC Characteristics

| Symbol | Parameter ⁽¹⁾ | M48Z128/Y | | M48Z128/Y/V | | M48Z128/Y/V | | Unit |
|------------------------------------|---|-----------|-----|-------------|-----|-------------|-----|------|
| | | -70 | | -85 | | -120 | | |
| | | Min | Max | Min | Max | Min | Max | |
| t _{AVAV} | WRITE Cycle Time | 70 | | 85 | | 120 | | ns |
| t _{AVWL} | Address Valid to WRITE Enable Low | 0 | | 0 | | 0 | | ns |
| t _{AVEL} | Address Valid to Chip Enable Low | 0 | | 0 | | 0 | | ns |
| t _{WLWH} | WRITE Enable Pulse Width | 55 | | 65 | | 85 | | ns |
| t _{ELEH} | Chip Enable Low to Chip Enable High | 55 | | 75 | | 100 | | ns |
| t _{WHAX} | WRITE Enable High to Address Transition | 5 | | 5 | | 5 | | ns |
| t _{EHAX} | Chip Enable High to Address Transition | 15 | | 15 | | 15 | | ns |
| t _{DVWH} | Input Valid to WRITE Enable High | 30 | | 35 | | 45 | | ns |
| t _{DVEH} | Input Valid to Chip Enable High | 30 | | 35 | | 45 | | ns |
| t _{WHDX} | WRITE Enable High to Input Transition | 0 | | 0 | | 0 | | ns |
| t _{EHDX} | Chip Enable High to Input Transition | 10 | | 10 | | 10 | | ns |
| t _{WLQZ} ^(2,3) | WRITE Enable Low to Output Hi-Z | | 25 | | 30 | | 40 | ns |
| t _{AVWH} | Address Valid to WRITE Enable High | 65 | | 75 | | 100 | | ns |
| t _{AVEH} | Address Valid to Chip Enable High | 65 | | 75 | | 100 | | ns |
| t _{WHQX} ^(2,3) | WRITE Enable High to Output Transition | 5 | | 5 | | 5 | | ns |

Note: 1. Valid for Ambient Operating Temperature: T_A = 0 to 70°C; V_{CC} = 4.75 to 5.5V, 4.5 to 5.5V or 3.0 to 3.6V (except where noted).
 2. C_L = 5pF.
 3. If \bar{E} goes low simultaneously with \bar{W} going low, the outputs remain in the high impedance state.

Data Retention Mode

With valid V_{CC} applied, the M48Z128/Y/V operates as a conventional BYTEWIDE™ static RAM. Should the supply voltage decay, the RAM will automatically power-fail deselect, write protecting itself t_{WP} after V_{CC} falls below V_{PFD} . All outputs become high impedance, and all inputs are treated as “Don't care.”

If power fail detection occurs during a valid access, the memory cycle continues to completion. If the memory cycle fails to terminate within the time t_{WP} , write protection takes place. When V_{CC} drops below V_{SO} , the control circuit switches power to the internal energy source which preserves data.

The internal coin cell will maintain data in the M48Z128/Y/V after the initial application of V_{CC} for an accumulated period of at least 10 years when V_{CC} is less than V_{SO} . As system power returns and V_{CC} rises above V_{SO} , the battery is disconnected, and the power supply is switched to external V_{CC} . Write protection continues for t_{ER} after V_{CC} reaches V_{PFD} to allow for processor stabilization. After t_{ER} , normal RAM operation can resume. For more information on Battery Storage Life refer to the Application Note AN1012.

Figure 11. Power Down/Up Mode AC Waveforms

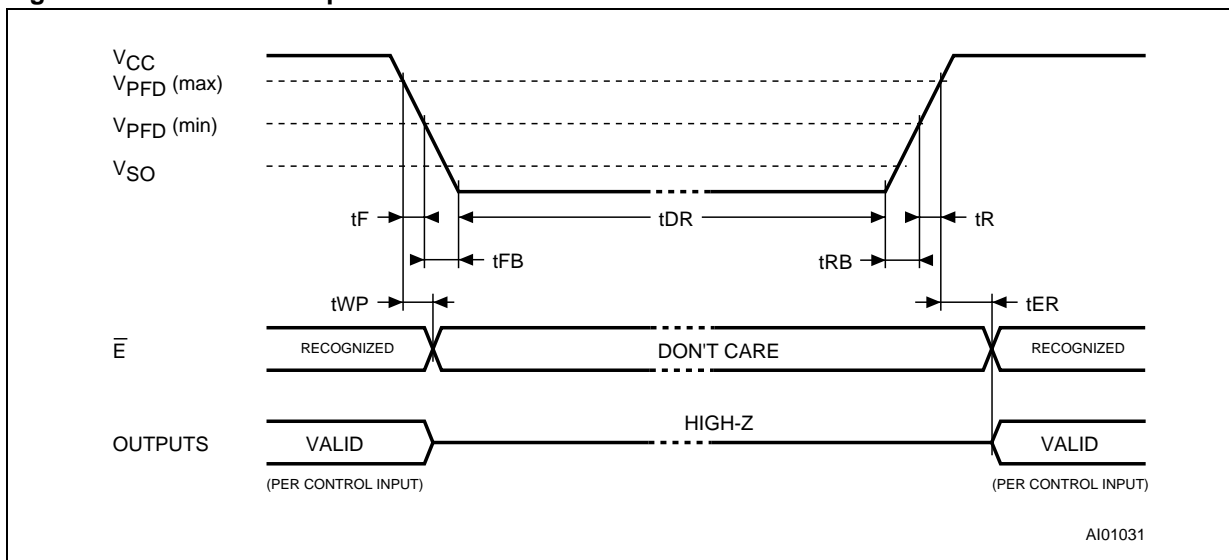


Table 10. Power Down/Up AC Characteristics

| Symbol | Parameter ⁽¹⁾ | Min | Max | Unit | |
|----------------|---|-----------|-----|---------------|---------------|
| $t_F^{(2)}$ | $V_{PFD}(\text{max})$ to $V_{PFD}(\text{min})$ V_{CC} Fall Time | 300 | | μs | |
| $t_{FB}^{(3)}$ | $V_{PFD}(\text{min})$ to V_{SS} V_{CC} Fall Time | M48Z128/Y | 10 | μs | |
| | | M48Z128V | 150 | | |
| t_R | $V_{PFD}(\text{min})$ to $V_{PFD}(\text{max})$ V_{CC} Rise Time | 10 | | μs | |
| t_{RB} | V_{SS} to $V_{PFD}(\text{min})$ V_{CC} Rise Time | 1 | | μs | |
| t_{WP} | Write Protect Time | M48Z128/Y | 40 | 150 | μs |
| | | M48Z128V | 40 | 250 | |
| t_{ER} | \bar{E} Recovery Time | 40 | 120 | ms | |

Note: 1. Valid for Ambient Operating Temperature: $T_A = 0$ to 70°C ; $V_{CC} = 4.75$ to 5.5V , 4.5 to 5.5V , or 3.0 to 3.6V (except where noted).
 2. $V_{PFD}(\text{max})$ to $V_{PFD}(\text{min})$ fall time of less than t_F may result in deselection/write protection not occurring until $200\mu\text{s}$ after V_{CC} passes $V_{PFD}(\text{min})$.
 3. $V_{PFD}(\text{min})$ to V_{SS} fall time of less than t_{FB} may cause corruption of RAM data.

Table 11. Power Down/Up Trip Points DC Characteristics

| Symbol | Parameter ^(1,2) | Min | Typ | Max | Unit | |
|--------------------------------|------------------------------------|-----------|-----|-----|-------|---|
| V _{PF} D | Power-fail Deselect Voltage | M48Z128 | 4.5 | 4.6 | 4.75 | V |
| | | M48Z128Y | 4.2 | 4.3 | 4.5 | V |
| | | M48Z128V | 2.8 | 2.9 | 3.0 | V |
| V _{SO} | Battery Back-up Switchover Voltage | M48Z128/Y | | 3.0 | | V |
| | | M48Z128V | | 2.5 | | V |
| t _{DR} ⁽³⁾ | Expected Data Retention Time | 10 | | | YEARS | |

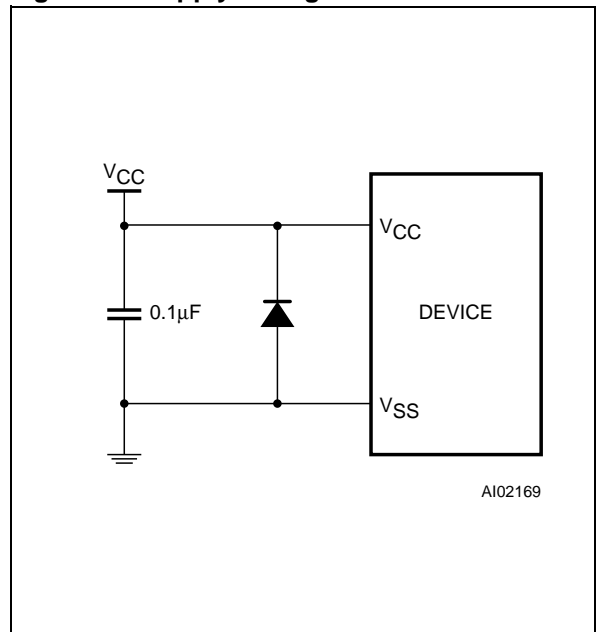
Note: 1. All voltages referenced to V_{SS}.
 2. Valid for Ambient Operating Temperature: T_A = 0 to 70°C; V_{CC} = 4.75 to 5.5V, 4.5 to 5.5V, or 3.0 to 3.6V (except where noted).
 3. At 25°C; V_{CC} = 0V.

V_{CC} Noise And Negative Going Transients

I_{CC} transients, including those produced by output switching, can produce voltage fluctuations, resulting in spikes on the V_{CC} bus. These transients can be reduced if capacitors are used to store energy which stabilizes the V_{CC} bus. The energy stored in the bypass capacitors will be released as low going spikes are generated or energy will be absorbed when overshoots occur. A ceramic bypass capacitor value of 0.1µF (see Figure 12) is recommended in order to provide the needed filtering.

In addition to transients that are caused by normal SRAM operation, power cycling can generate negative voltage spikes on V_{CC} that drive it to values below V_{SS} by as much as one volt. These negative spikes can cause data corruption in the SRAM while in battery backup mode. To protect from these voltage spikes, ST recommends connecting a schottky diode from V_{CC} to V_{SS} (cathode connected to V_{CC}, anode to V_{SS}). (Schottky diode 1N5817 is recommended for through hole and MBRS120T3 is recommended for surface-mount).

Figure 12. Supply Voltage Protection



PART NUMBERING

Table 12. Ordering Information Scheme

| | | | | | |
|--|------|------|-----|----|---|
| Example: | M48Z | 128Y | -70 | PM | 1 |
| Device Type | | | | | |
| M48Z | | | | | |
| Supply Voltage and Write Protect Voltage | | | | | |
| 128 = $V_{CC} = 4.75$ to $5.5V$; $V_{PFD} = 4.5$ to $4.75V$ | | | | | |
| 128Y = $V_{CC} = 4.5$ to $5.5V$; $V_{PFD} = 4.2$ to $4.5V$ | | | | | |
| 128V ⁽¹⁾ = $V_{CC} = 3.0$ to $3.6V$; $V_{PFD} = 2.8$ to $3.0V$ | | | | | |
| Speed | | | | | |
| -70 = 70ns (for M48Z128/Y) | | | | | |
| -85 = 85ns (for M48Z128/Y/V) | | | | | |
| -120 = 120ns (for M48Z128/Y/V) | | | | | |
| Package⁽²⁾ | | | | | |
| PM = PMDIP32 | | | | | |
| Temperature Range | | | | | |
| 1 = 0 to 70°C | | | | | |

Note: 1. Contact Local Sales Office

2. The SOIC package (SOH28) requires the battery package (SNAPHAT[®]) which is ordered separately under the part number "M4Zxx-BR00SH" in plastic tube or "M4Zxx-BR00SHTR" in Tape & Reel form.

Caution: Do not place the SNAPHAT battery package "M4Zxx-BR00SH" in conductive foam as it will drain the lithium button-cell battery.

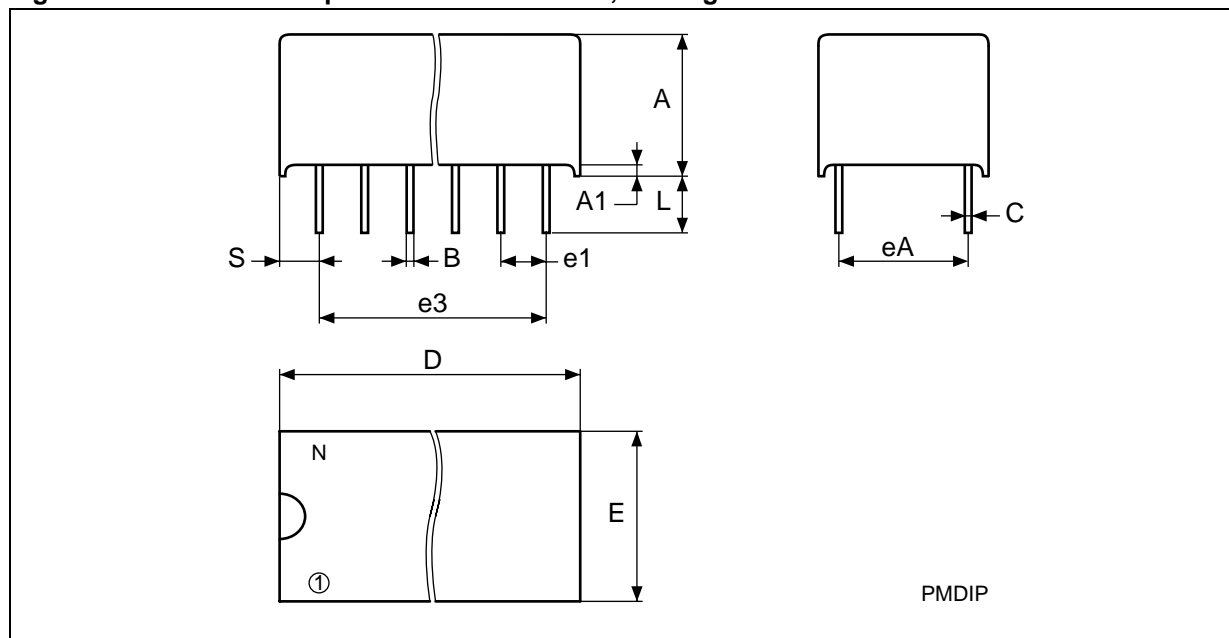
For a list of available options (e.g., Speed, Package) or for further information on any aspect of this device, please contact the ST Sales Office nearest to you.

Table 13. SNAPHAT Battery Table

| Part Number | Description | Package |
|--------------|----------------------------------|---------|
| M4Z28-BR00SH | Lithium Battery (48mAh) SNAPHAT | SH |
| M4Z32-BR00SH | Lithium Battery (120mAh) SNAPHAT | SH |

PACKAGE MECHANICAL INFORMATION

Figure 13. PMDIP32 – 32-pin Plastic DIP Module, Package Outline

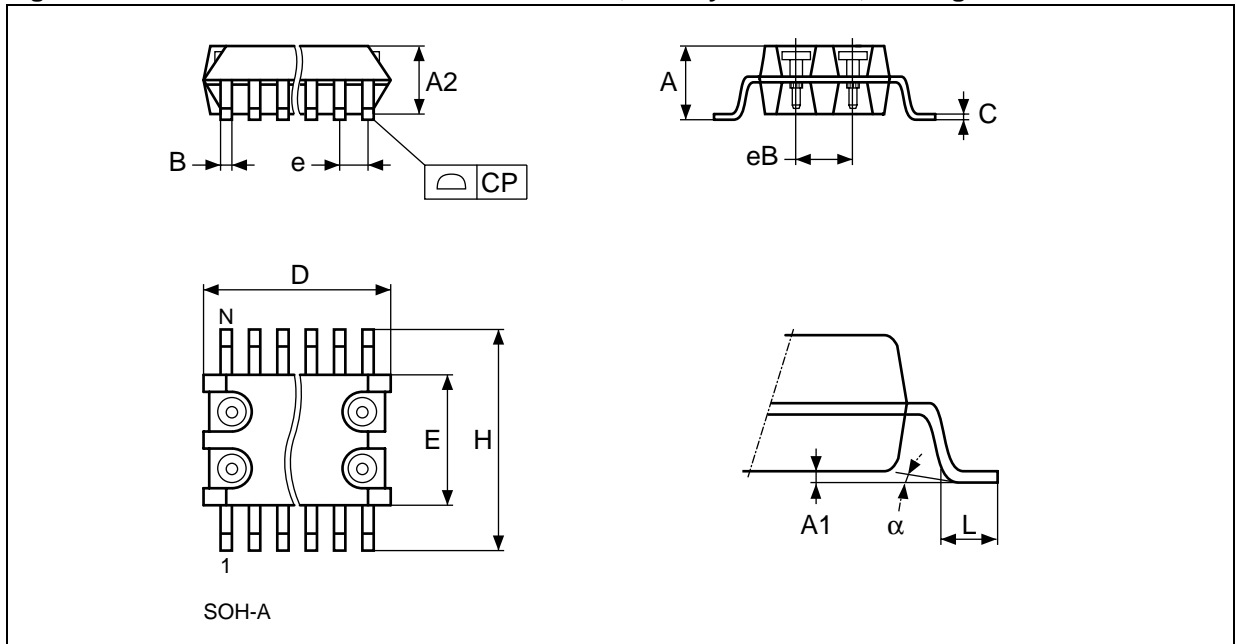


Note: Drawing is not to scale.

Table 14. PMDIP32 – 32-pin Plastic DIP Module, Package Mechanical Data

| Symb | mm | | | inches | | |
|------|-----|-------|-------|--------|-------|-------|
| | Typ | Min | Max | Typ | Min | Max |
| A | | 9.27 | 9.52 | | 0.365 | 0.375 |
| A1 | | 0.38 | – | | 0.015 | – |
| B | | 0.43 | 0.59 | | 0.017 | 0.023 |
| C | | 0.20 | 0.33 | | 0.008 | 0.013 |
| D | | 42.42 | 43.18 | | 1.670 | 1.700 |
| E | | 18.03 | 18.80 | | 0.710 | 0.740 |
| e1 | | 2.29 | 2.79 | | 0.090 | 0.110 |
| e3 | | 34.29 | 41.91 | | 1.350 | 1.650 |
| eA | | 14.99 | 16.00 | | 0.590 | 0.630 |
| L | | 3.05 | 3.81 | | 0.120 | 0.150 |
| S | | 1.91 | 2.79 | | 0.075 | 0.110 |
| N | | 32 | | | 32 | |

Figure 14. SOH28 – 28-lead Plastic Small Outline, battery SNAPHAT, Package Outline

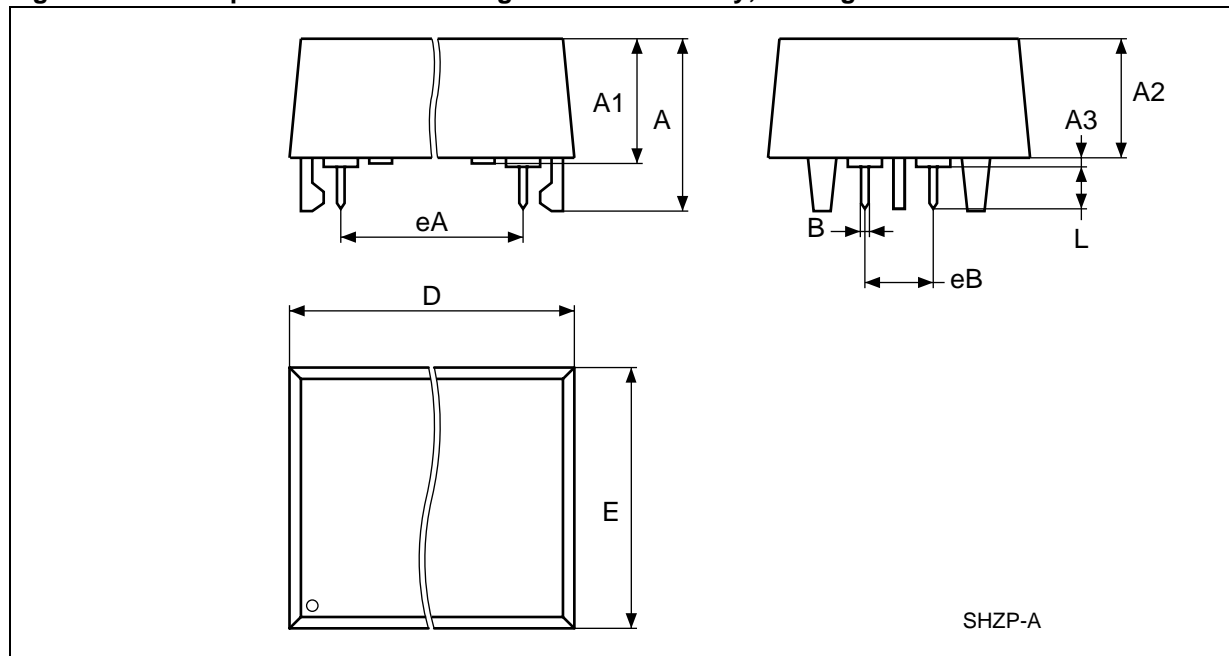


Note: Drawing is not to scale.

Table 15. SOH28 – 28-lead Plastic Small Outline, battery SNAPHAT, Package Mechanical Data

| Symbol | mm | | | inch | | |
|----------|------|-------|-------|-------|-------|-------|
| | Typ | Min | Max | Typ | Min | Max |
| A | | | 3.05 | | | 0.120 |
| A1 | | 0.05 | 0.36 | | 0.002 | 0.014 |
| A2 | | 2.34 | 2.69 | | 0.092 | 0.106 |
| B | | 0.36 | 0.51 | | 0.014 | 0.020 |
| C | | 0.15 | 0.32 | | 0.006 | 0.012 |
| D | | 17.71 | 18.49 | | 0.697 | 0.728 |
| E | | 8.23 | 8.89 | | 0.324 | 0.350 |
| e | 1.27 | – | – | 0.050 | – | – |
| eB | | 3.20 | 3.61 | | 0.126 | 0.142 |
| H | | 11.51 | 12.70 | | 0.453 | 0.500 |
| L | | 0.41 | 1.27 | | 0.016 | 0.050 |
| α | | 0° | 8° | | 0° | 8° |
| N | | 28 | | | 28 | |
| CP | | | 0.10 | | | 0.004 |

Figure 15. SH – 4-pin SNAPHAT Housing for 48mAh Battery, Package Outline

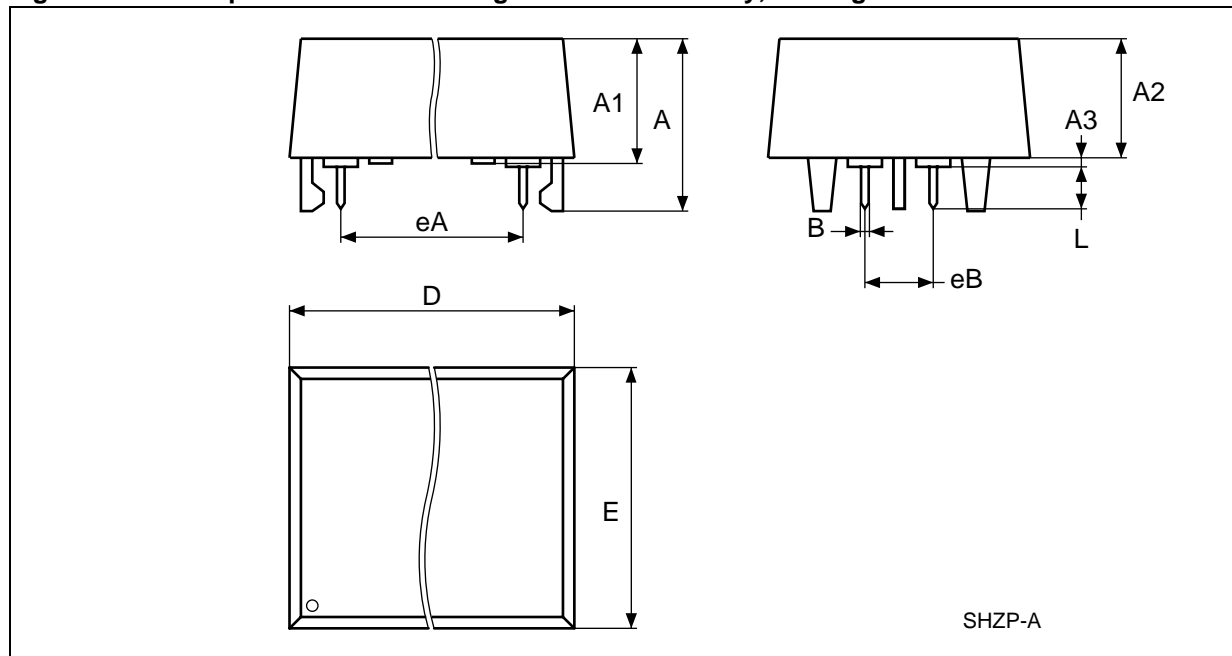


Note: Drawing is not to scale.

Table 16. SH – 4-pin SNAPHAT Housing for 48mAh Battery, Package Mechanical Data

| Symb | mm | | | inches | | |
|------|-----|-------|-------|--------|-------|-------|
| | Typ | Min | Max | Typ | Min | Max |
| A | | | 9.78 | | | 0.385 |
| A1 | | 6.73 | 7.24 | | 0.265 | 0.285 |
| A2 | | 6.48 | 6.99 | | 0.255 | 0.275 |
| A3 | | | 0.38 | | | 0.015 |
| B | | 0.46 | 0.56 | | 0.018 | 0.022 |
| D | | 21.21 | 21.84 | | 0.835 | 0.860 |
| E | | 14.22 | 14.99 | | 0.560 | 0.590 |
| eA | | 15.55 | 15.95 | | 0.612 | 0.628 |
| eB | | 3.20 | 3.61 | | 0.126 | 0.142 |
| L | | 2.03 | 2.29 | | 0.080 | 0.090 |

Figure 16. SH – 4-pin SNAPHAT Housing for 120mAh Battery, Package Outline



Note: Drawing is not to scale.

Table 17. SH – 4-pin SNAPHAT Housing for 120mAh Battery, Package Mechanical Data

| Symb | mm | | | inches | | |
|------|-----|-------|-------|--------|-------|-------|
| | Typ | Min | Max | Typ | Min | Max |
| A | | | 10.54 | | | 0.415 |
| A1 | | 8.00 | 8.51 | | 0.315 | 0.335 |
| A2 | | 7.24 | 8.00 | | 0.285 | 0.315 |
| A3 | | | 0.38 | | | 0.015 |
| B | | 0.46 | 0.56 | | 0.018 | 0.022 |
| D | | 21.21 | 21.84 | | 0.835 | 0.860 |
| E | | 17.27 | 18.03 | | 0.680 | 0.710 |
| eA | | 15.55 | 15.95 | | 0.612 | 0.628 |
| eB | | 3.20 | 3.61 | | 0.126 | 0.142 |
| L | | 2.03 | 2.29 | | 0.080 | 0.090 |

REVISION HISTORY**Table 18. Revision History**

| Date | Rev. # | Revision Details |
|-------------|---------------|--|
| May 1999 | 1.0 | First Issue |
| 13-Apr-00 | 2.0 | Document Layout changed; surface-Mount Chip Set solution added |
| 20-Jun-00 | 2.1 | t _{GLQX} changed (Table 8) |
| 19-Jul-00 | 2.2 | M48Z128V added |
| 14-Sep-01 | 3.0 | Reformatted; added temperature information (Table 5, 6, 8, 9, 10, 11) |
| 07-Nov-01 | 3.1 | Remove chipset option from Ordering Information (Table 12) |
| 20-May-02 | 3.2 | Modify reflow time and temperature footnotes (Table 3) |
| 18-Nov-02 | 3.3 | Modifying SMT solution text (Figure 2, 5; Table 2) |
| 17-Sep-03 | 3.4 | Remove references to M68ZXXX (obsolete) parts (Figure 5; Table 2); update disclaimer |

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